

# 1SS355

## SILICON EPITAXIAL HIGH SPEED SWITCHING DIODE

### FEATURES :

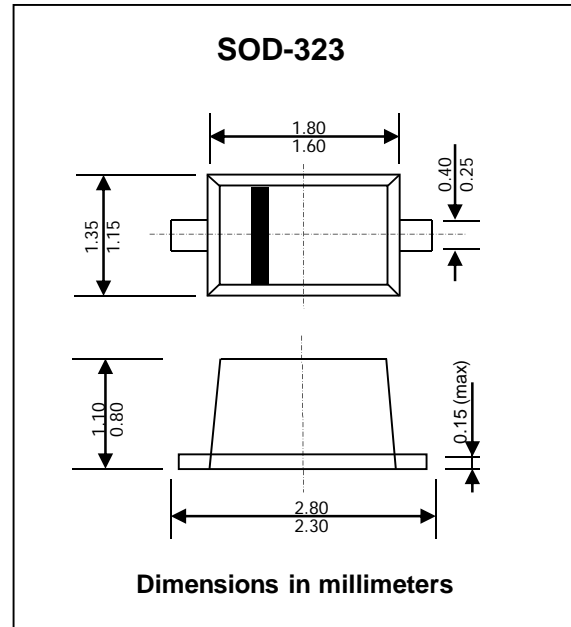
- Small plastic package suitable for surface mounted design
- High reliability with high surge current handling capability
- Pb / RoHS Free

### APPLICATIONS

- High speed switching

### MECHANICAL DATA :

- Case : SOD-123
- Marking Code : " W2 "



### Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RRM}$	90	V
Maximum DC Reverse Voltage	$V_{RM}$	80	V
Maximum Average Forward Current	$I_F$	100	mA
Maximum Peak Forward Current	$I_{FM}$	255	mA
Maximum Surge Current (1s)	$I_{FSM}$	500	mA
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_S$	-55 to + 150	°C

### Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 100 \text{ mA}$	-	-	1.2	V
Reverse Current	$I_R$	$V_R = 80 \text{ V}$	-	-	0.1	$\mu\text{A}$
Capacitance between terminals	$C_T$	$f = 1\text{MHz} ; V_R = 0.5$	-	-	3.0	pF
Reverse Recovery Time	$T_{rr}$	$I_F = 10 \text{ mA} , V_R = 6 \text{ V}$ $R_L = 100 \Omega$	-	-	4.0	ns

## RATING AND CHARACTERISTIC CURVES ( 1SS355 )

FIG.1 - FORWARD CURRENT DERATING CURVE

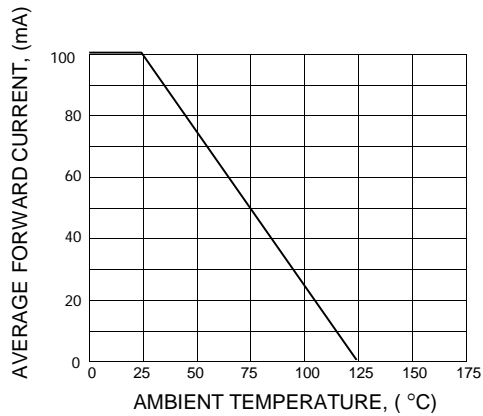


FIG.2 - MAXIMUM SURGE CURRENT

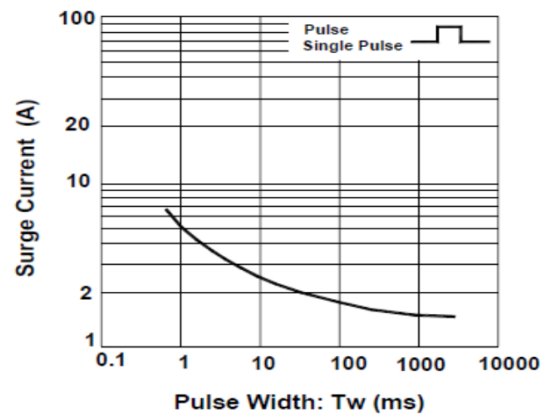


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

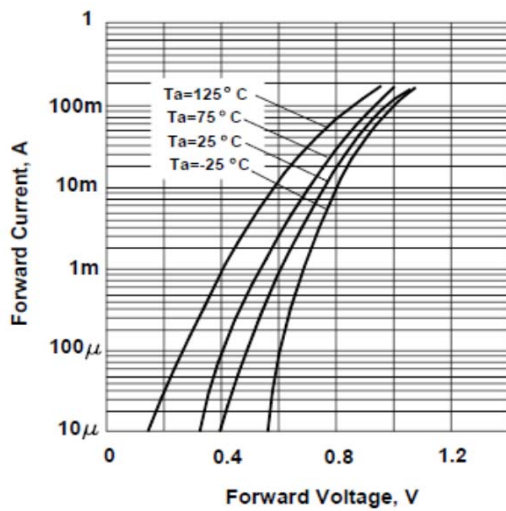


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

